

## Silicon NPN Power Transistor

### DESCRIPTION

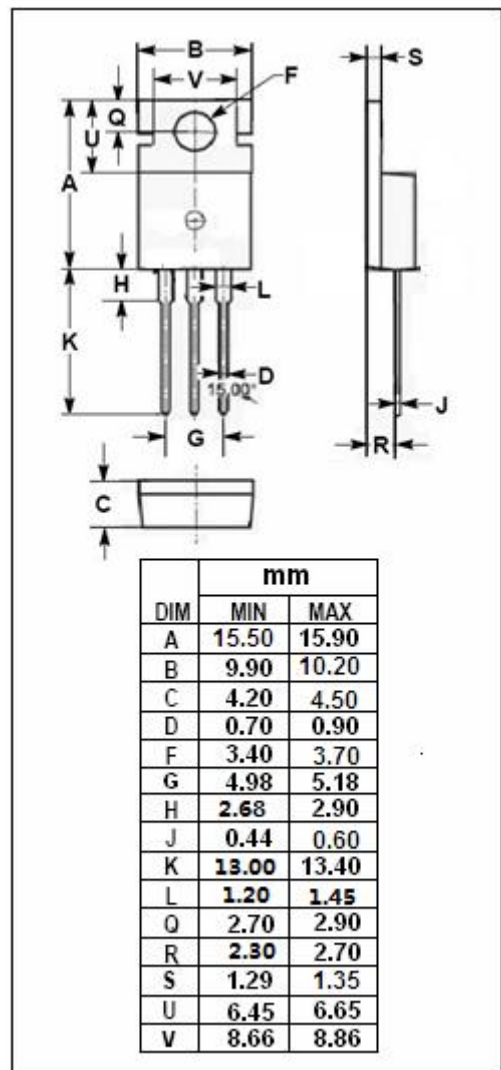
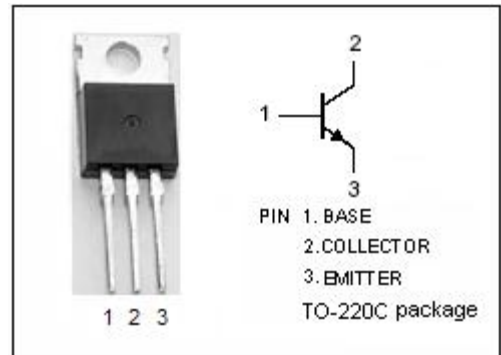
- Collector-Emitter Breakdown Voltage-  
:V<sub>(BR)CEO</sub>= 150V(Min)
- Wide Area of Safe Operation
- Complement to Type 2SA940

### APPLICATIONS

- Power amplifier applications.
- Vertical output applications.

### ABSOLUTE MAXIMUM RATINGS(T<sub>a</sub>=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V <sub>CBO</sub>	Collector-Base Voltage	150	V
V <sub>CEO</sub>	Collector-Emitter Voltage	150	V
V <sub>EBO</sub>	Emitter-Base Voltage	5	V
I <sub>C</sub>	Collector Current-Continuous	1.5	A
I <sub>B</sub>	Base Current-Continuous	0.5	A
P <sub>C</sub>	Collector Power Dissipation @ T <sub>a</sub> =25°C	1.5	W
	Collector Power Dissipation @ T <sub>c</sub> =25°C	25	
T <sub>J</sub>	Junction Temperature	150	°C
T <sub>stg</sub>	Storage Temperature Range	-55~150	°C



### Ordering Information

Product	Package	Packaging
2SC2073T1TL	TO-220C	Tube



## ELECTRICAL CHARACTERISTICS

$T_c=25^{\circ}\text{C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=500\text{mA}; I_B=50\text{mA}$			1.5	V
$V_{BE(on)}$	Base-Emitter On Voltage	$I_C=500\text{mA}; V_{CE}=10\text{V}$			0.85	V
$I_{CBO}$	Collector Cutoff Current	$V_{CB}=120\text{V}; I_E=0$			10	$\mu\text{A}$
$I_{EBO}$	Emitter Cutoff Current	$V_{EB}=5\text{V}; I_C=0$			10	$\mu\text{A}$
$h_{FE}$	DC Current Gain	$I_C=500\text{mA}; V_{CE}=10\text{V}$	40		140	
$C_{OB}$	Output Capacitance	$I_E=0; V_{CB}=10\text{V}; f_{test}=1\text{MHz}$		35		pF
$f_T$	Current-Gain—Bandwidth Product	$I_C=500\text{mA}; V_{CE}=10\text{V}$		4		MHz